







# Developments In DDR Main Memory Platform Design

February 15, 2001





# Agenda

-  **DDR standard update**
-  **DDR systems implementations today**
-  **Improving DDR channel bandwidth**
-  **Migrating to DDR333/PC2700**



# DDR Standard Update



# The DDR Standard

- ✚ All standards are in place
  - ? Components and modules
- ✚ There have been a few minor tweaks
  - ? Addition of four new SPD bits to better define module performance capability
- ✚ On-line access to the latest data
  - ? JEDEC Web site
  - ? Micron Design Toolbox at <http://reg.muscp.com/mk/get/TOOLBOXREG>



# DDR SPD



**Byte 41 added to define  $t_{RC_{min}}$**

- ? Have been using Byte 27 ( $t_{RP_{min}}$ ) + Byte 30 ( $t_{RAS_{min}}$ )
- ?  $t_{RP_{min}} + t_{RAS_{min}}$  do not always equal  $t_{RC_{min}}$
- ?  $t_{RC_{min}}$  must be defined by using Byte 41



**Byte 42 added to define  $t_{RFC_{min}}$**

- ? Refresh cycle rate use READ/WRITE cycle rate  $t_{RC_{min}}$
- ?  $t_{RFC_{min}}$  is one or two clocks longer than  $t_{RC_{min}}$
- ? Refresh cycle rate must use refresh cycle rate -  $t_{RFC_{min}}$



# DDR SPD

 Byte 22 supports two new optional features

? Bit 6 defines Concurrent Autoprecharge (AP) support

 1 indicates support for optional feature

 0 indicates no support for optional feature

? Bit 7 defines RAS lockout support

 Applies only when AP is enabled

- $t_{RCD}$  is replaced by  $t_{RAP}$  when AP is enabled

 1 indicates support for optional feature

- $t_{RAP_{min}} = t_{RCD_{min}}$

 0 indicates no support for optional feature

- $t_{RAP_{min}} = t_{RAS_{min}} - t_{CK} * (\text{Burst Length divide by 2})$



# Today's DDR designs



# PC1600/2100 DDR Design Assumptions

- 📦 **Module designs assumed DDR—only memory systems**
- 📦 **Mixed SDR/DDR systems exist for cost/availability hedge today**
  - ? **Give many an opportunity to assess new technology in the second generation designs**
  - ? **Opportunities to assess cost reduction or higher performance options**





# Desktop

## Motherboards taking many forms

? DDR cost and availability has generated mixed SDR - DDR systems

 The standard has not included this kind of design

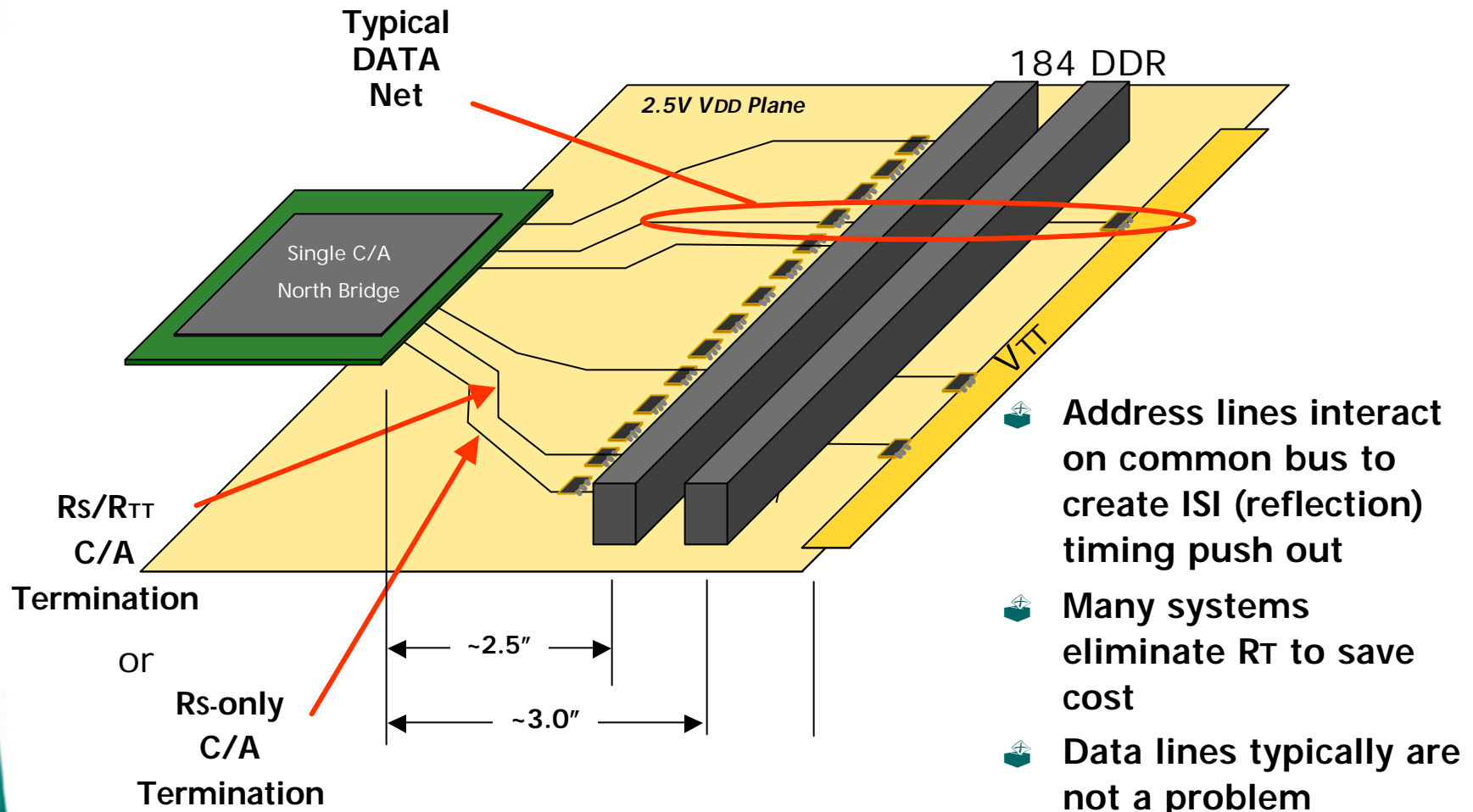
 Recommend caution; thoroughly test such systems

 These designs push the design parameters of DDR and PC133 SDR



# Example of Pure DDR Channel

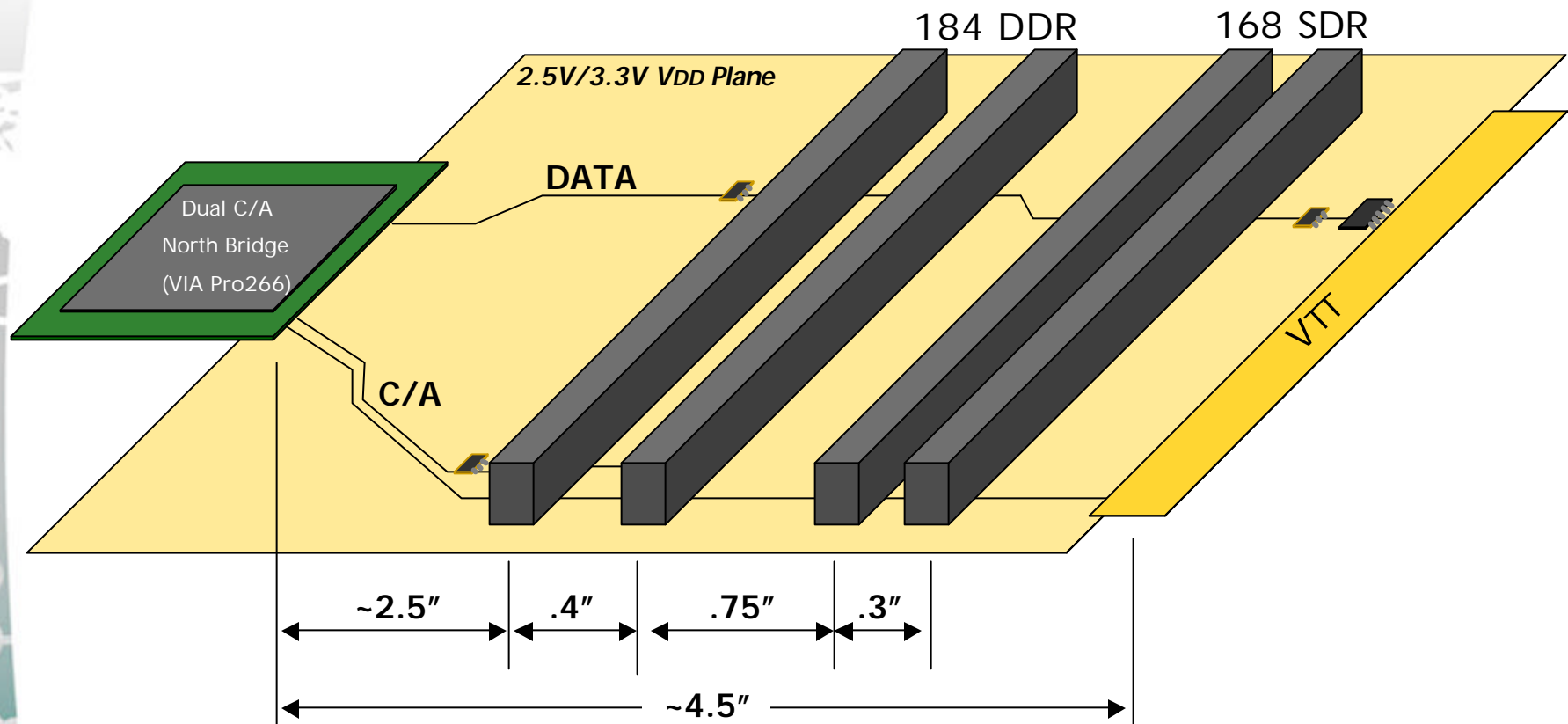
## 1 Copy, 2 Unbuffered DIMMs





# Mixed DDR/SDR System

## One of Many Examples



2T addressing - OK

Data load limited to 2 DIMMs at a time



# Desktop Implementations

## Type A, PC2100

? 2-copy C/A, 3 Unbuffered DIMMs, 2T per command

## Type B, PC2100

? 1-copy C/A, 2 Unbuffered DIMMs, 2T per command

? Even some trying 3 here, with some success

## Type C, PC2100

? 2-copy C/A, 2 Unbuffered DIMMs, 1T per command

## Ultimate goal, PC2700

? 1-copy C/A, 2 Unbuffered DIMM, 1T per command



# Server

- ✚ Traditional chassis with 1.7" Registered DIMMs
- ✚ 1U interest is very high
  - ? Reduced-height Registered DIMM is being addressed by standards groups; JEDEC, JEITA
  - ? Micron is in development of a 1.125" Registered DIMM for PC1600 and PC2100 systems
    - ✚ FBGA packaging for SDRAM
    - ✚ Meets all electrical characteristics of common TSOP-based common Gerber
    - ✚ 256MB and 512MB samples 2Q01; production 3Q01
    - ✚ Evolutionary to PC2700 Registered DIMM



# Server

## 4 DIMM/channel, PC1600

- ? Standard termination, series-R and parallel to VTT
- ? Systems running very stable at this speed

## 4 DIMM/channel

### ? Two possibilities

#### 2-copy C/A, 2 Registered DIMMs per copy, 1T command

- Standard termination
- High-performance, flip-chip BGA for ASIC

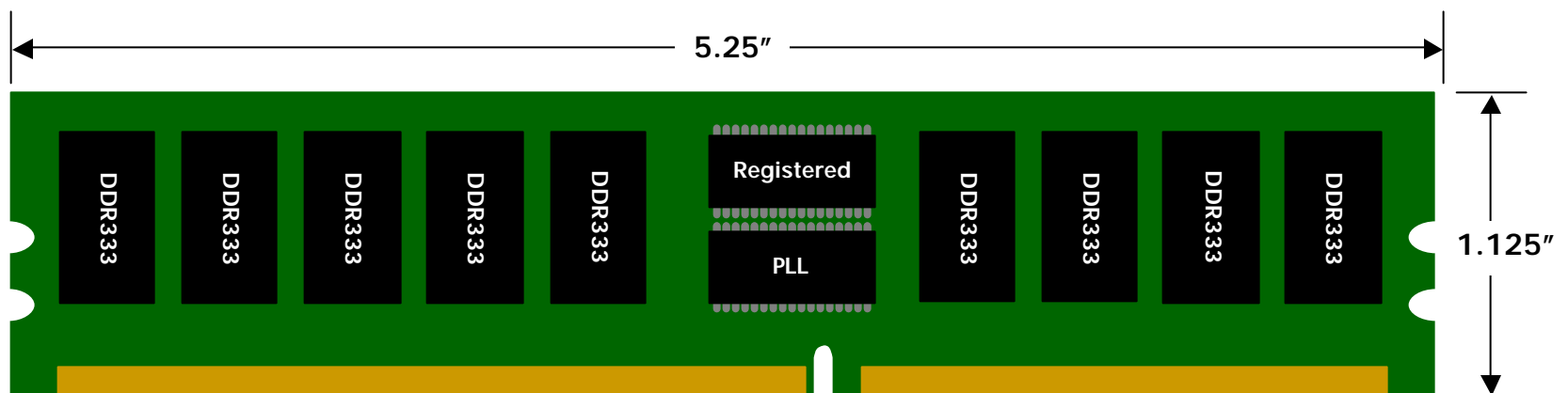
#### 1-copy C/A

- Requires new termination: capacitive-compensated
- Standard, wire-bond BGA package



# Low-Profile Registered DIMM

- ❏ FBGA SDRAM package, JEDEC registration
- ❏ Designed to match TSOP-based module topology and timing as closely as possible



- ❏ Provides a 90° (no angled sockets) solution for 1U servers



# Notebook

- ✦ **DDR SODIMMs are available**
  - ? Common Gerbers are done and production ready
- ✦ **DDR has a big power advantage over PC133**
  - ? Current system benchmarks showing approximately 30% lower power than PC133
  - ? This at the 2X bandwidth of DDR266/PC2100!
- ✦ **Mechanical design very similar to SDR**
  - ? Most systems can be designed without major changes to cases



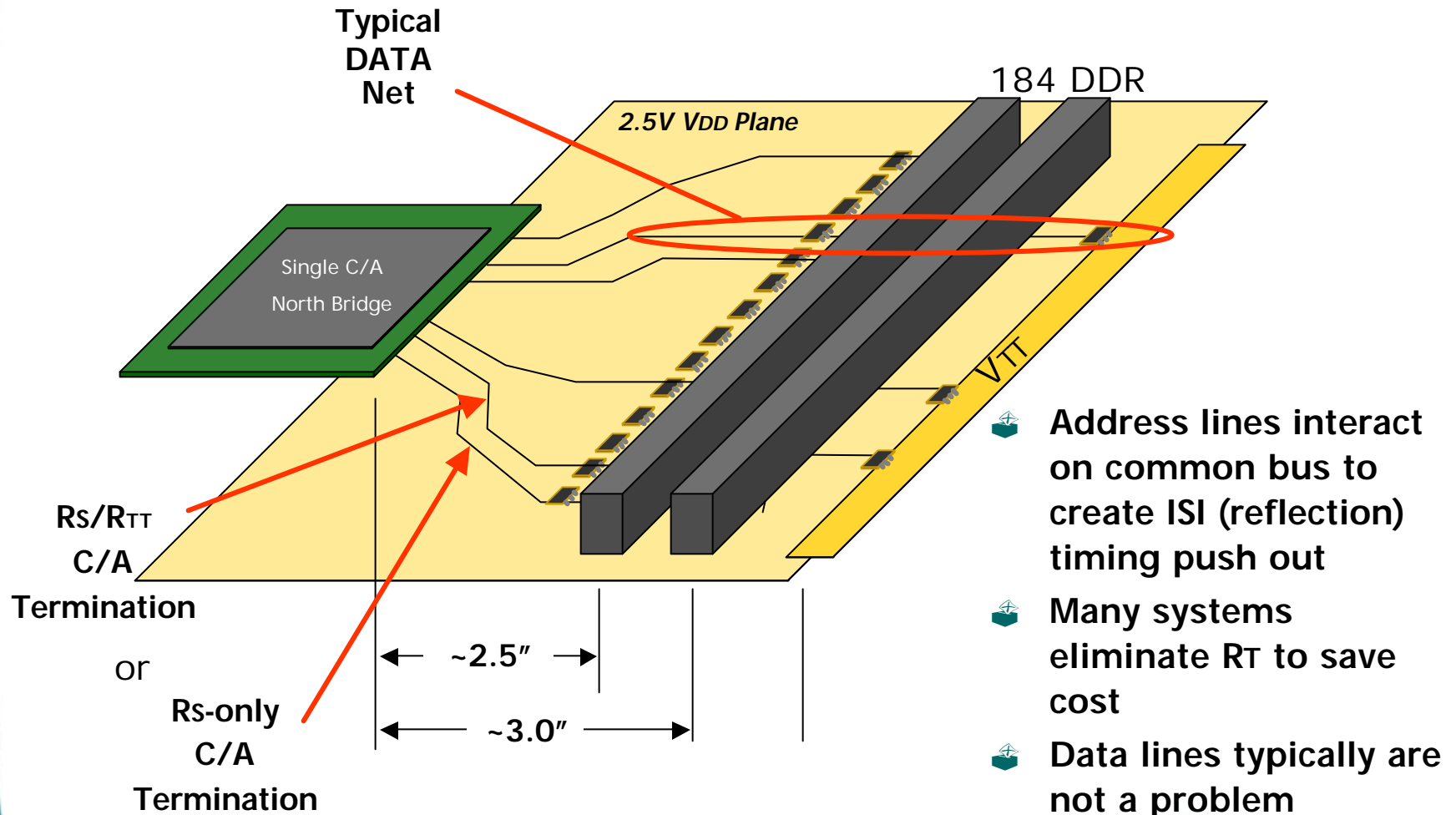


# Second Generation DDR Design



# Example of Typical DDR Channel

## 1 Copy, 2 Unbuffered DIMMs



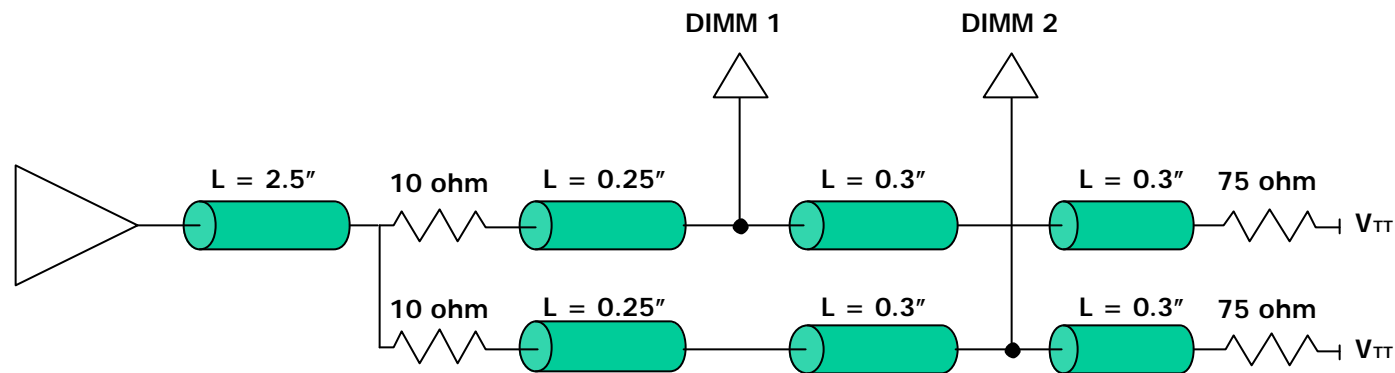


# Getting More Bandwidth

- ✦ **Techniques for better margin, little added cost**
  - ? Improved termination schemes for motherboard
  - ? Active termination in chipset
- ✦ **Improved interoperability due to increases in system margin at high frequency, mixed loads**
- ✦ **Provides a “spring board” to move motherboard designs to PC2700**



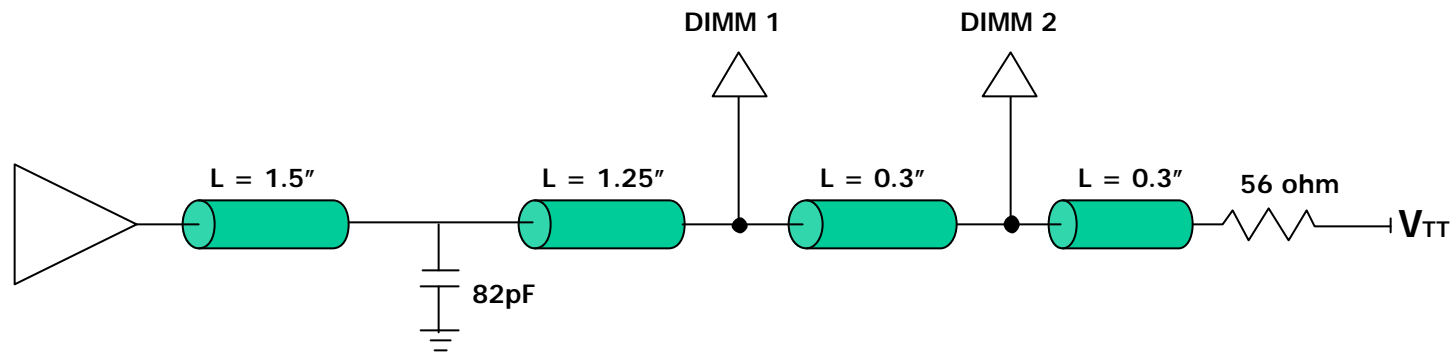
# Split-Bus Termination for Command/Address Bus



- Example C/A route
- Splitting bus isolates the DIMM loads from one another
- I/O power reduced over standard termination by using high value  $R_{TT}$
- No changes to ASIC driver necessary to see improvements
- Works with all DDR DIMM common Gerbers



# Capacitive Compensation Termination for Command/Address Bus



- Example C/A route
- Capacitor tunes frequency response of channel to limit ISI/reflections
- Some added propagation delay added due to R/C
- No changes to ASIC driver necessary to see improvements
- Works with all DDR DIMM common Gerbers

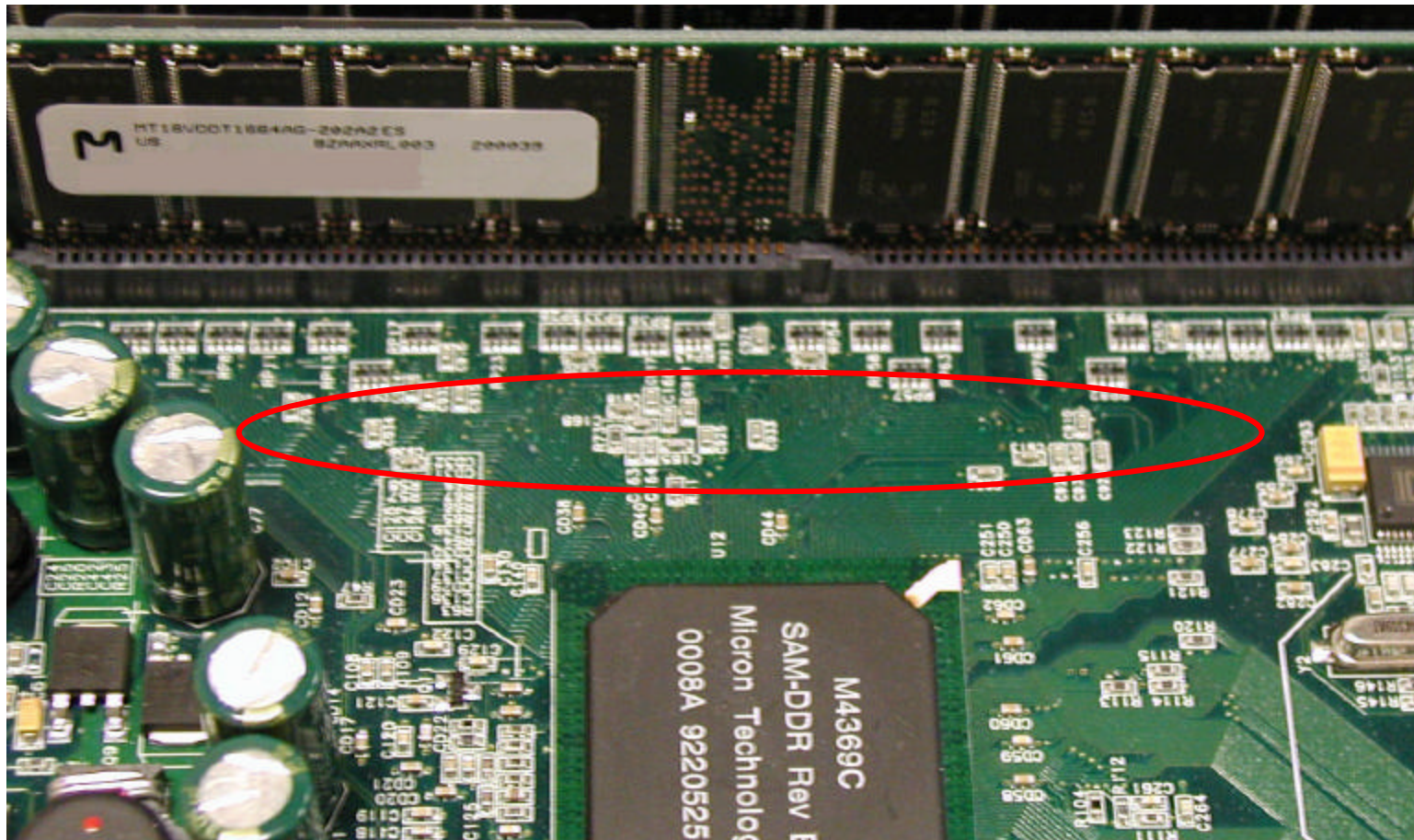




# Micron Hurricane Board

With Compensated C/A Net

🏠 Capacitive compensation of 82pF on Command/Address



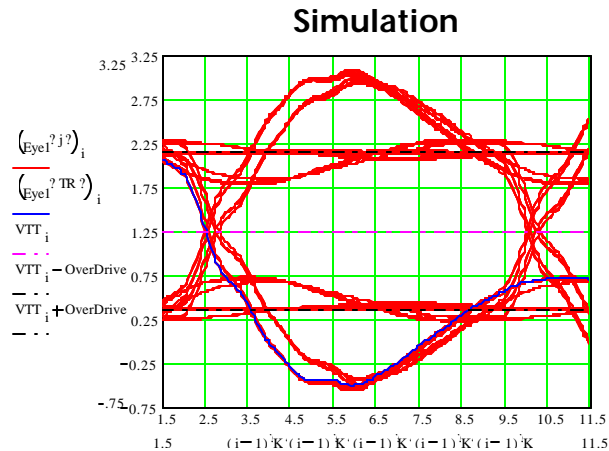


# Correlating Systems to Simulation

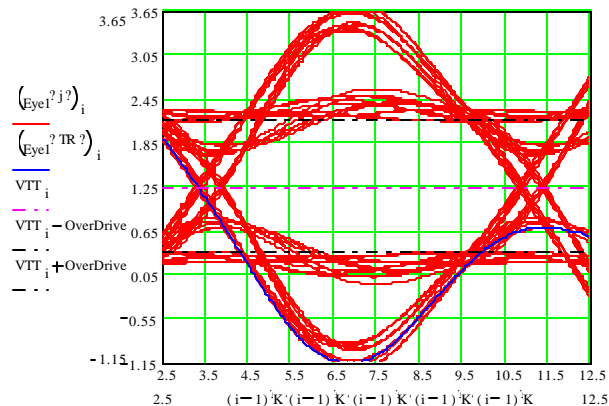
1st Slot: 4 Devices, 2nd Slot: None (Monitoring 1st Slot)

(Note: Scale change from non-compensated to compensated)

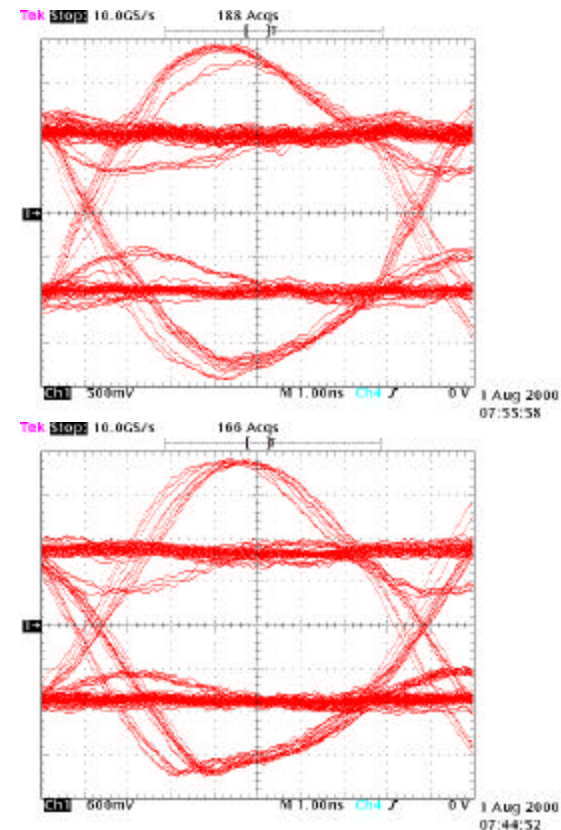
Non-Compensated  
Rs = 10 ohms  
Fcap = none



Compensated  
Rs = none  
Fcap = 82pF



Hardware Measurement



The modeling technology used by Micron has excellent correlation to actual systems





# Command/Address Loading

📦 Command rates possible at PC2100/DDR266

<i>C/A Bus</i>	<i>R<sub>s</sub></i>	<i>R<sub>s</sub>/R<sub>TT</sub></i>	<i>R<sub>TT</sub></i>	<i>C/R<sub>TT</sub></i>	<i>2xR<sub>s</sub>/R<sub>TT</sub></i>
1 Copy, 2 DIMM	2T	2T	2T	1T	1T
2 Copy, 2 DIMM	1T	1T	1T	1T	N/A





# Worst-Case Corner at PC2100

- ❏ 2 Unbuffered DIMMs, single-copy C/A system
  - ? Mixing DIMM loads can create reflection/ISI noise on edges of Command/Address
    - ❏ Light-load, 4-component DIMM in front slot;  
heavy-load, 16-component DIMM in the second slot
    - ❏ ASIC driver will affect the impact of module loading as well
  - ? Some only running with RS for termination on C/A
- ❏ Data net is much better balanced
  - ❏ Modules are only 1 or 2 loads per slot



# PC2100 Command Rate Targets

✚ Today all single-copy C/A systems are running 2T command rate (clocks per command)

? Systems with only RS will only run here

✚ The goal



? Embedded Northbridges (3D on-board) want to run 1T command rate, with a single C/A copy

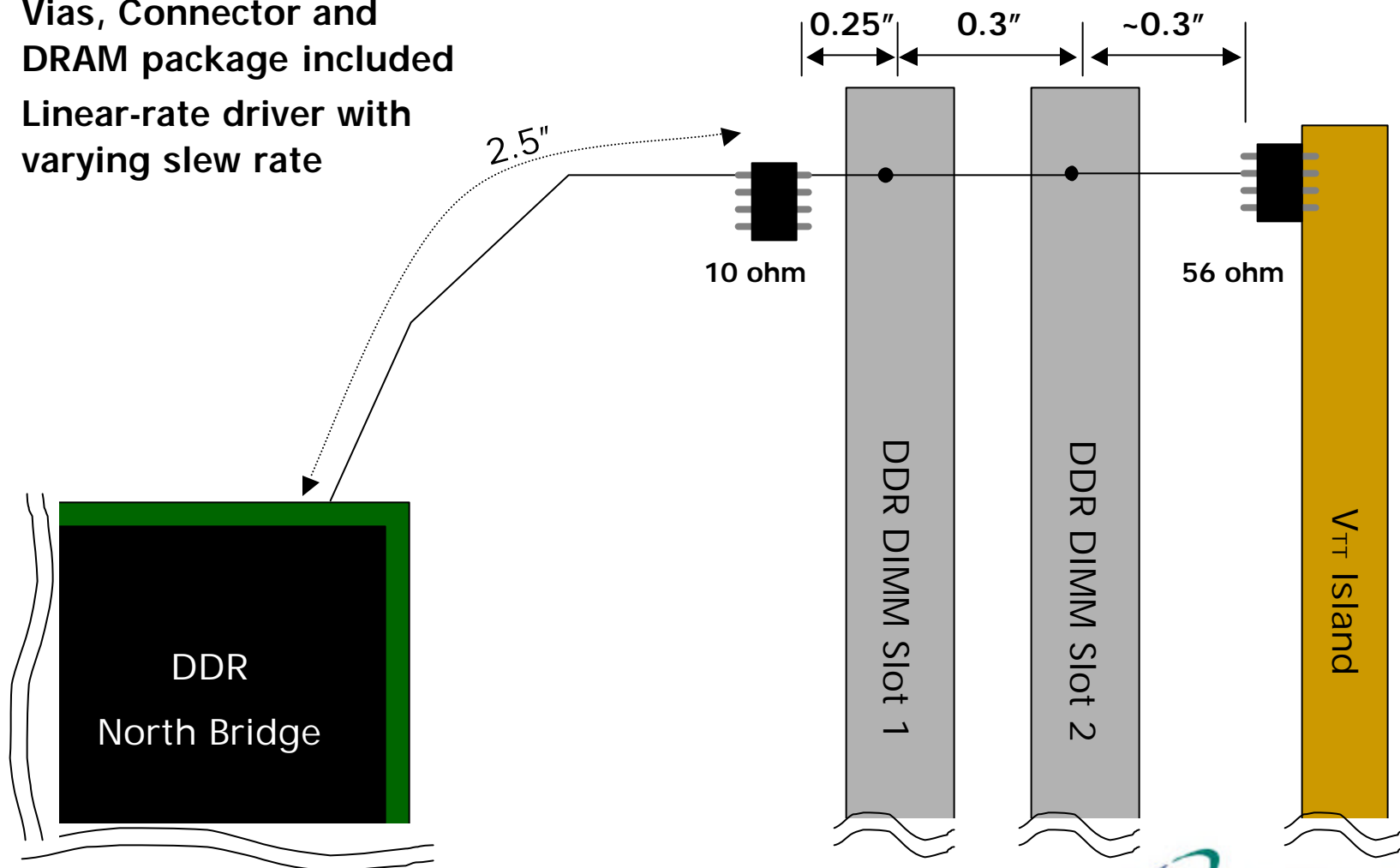
? Termination and board layout must be improved to accomplish this

? Limit cost adders, but can't avoid some added cost



# Simulation of Mixed DIMM

-  Vias, Connector and DRAM package included
-  Linear-rate driver with varying slew rate



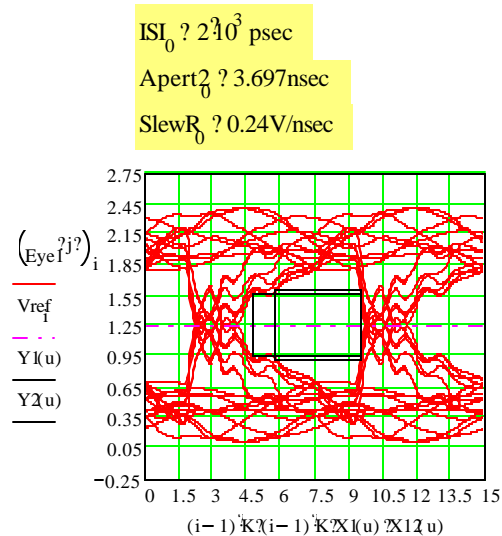


# Simulation of Mixed DIMM

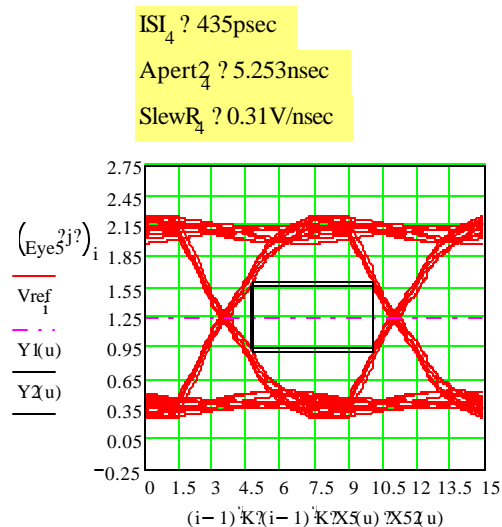
Input Slew Rate ~ 5V/ns

Slot 1 - 5 Devices, Slot 2 - 18 Devices

Slot 1



Slot 2



Standard termination

First DIMM shows eye reduction due to ISI

Topology mismatch between two DIMMs creates reduction

Second DIMM has well-defined eye

Worst case for this topology

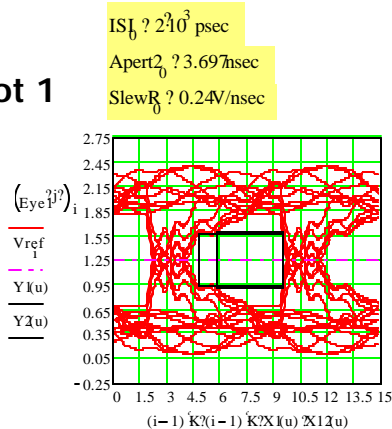


# Improved-Performance Scenarios

Input Slew Rate ~ 5V/ns  
Slot 1 - 5 Devices, Slot 2 - 18 Devices

## Standard

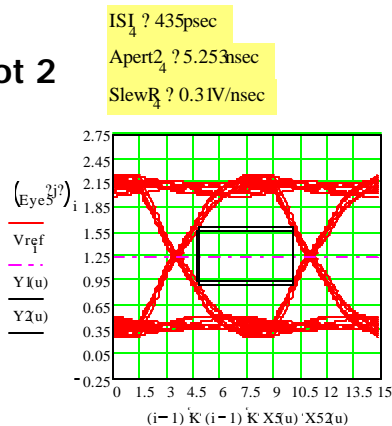
### Slot 1



Improvements to  
eye aperture and  
voltage level  
Large reduction  
in noise  
component



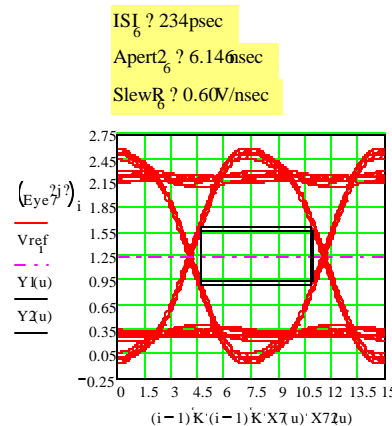
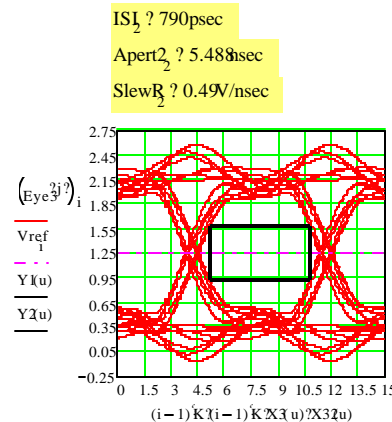
### Slot 2



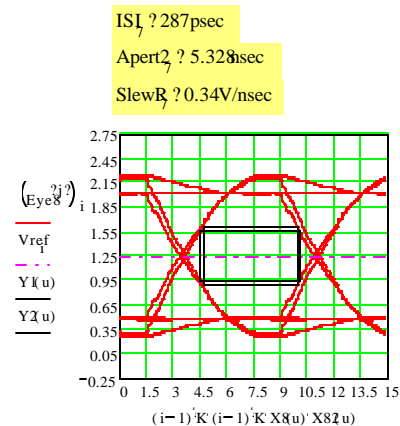
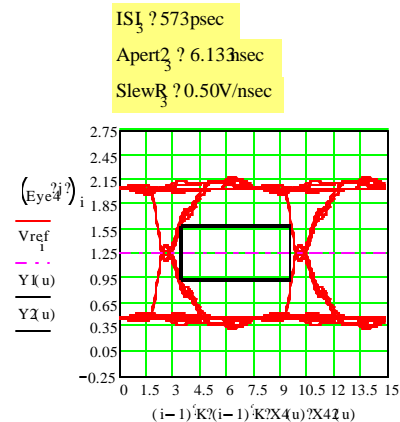
Improvements to  
eye aperture and  
voltage level



## Compensated



## Split Bus



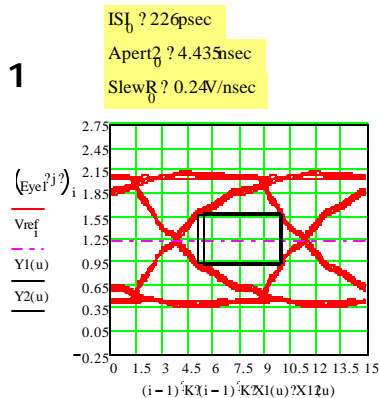


# Improved-Performance Scenarios

Input Slew Rate ~ 5V/ns  
Slot 1 - 18 Devices, Slot 2 - 18 Devices

Standard

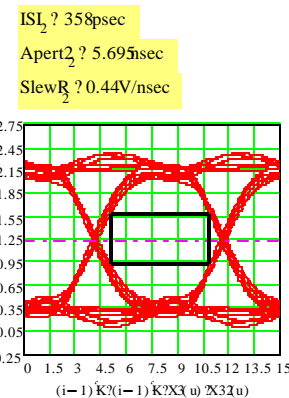
Slot 1



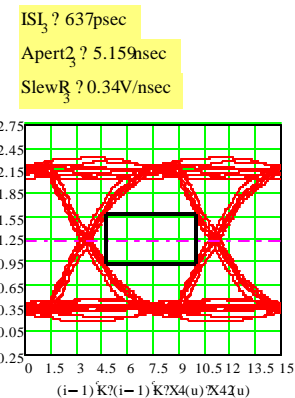
Improvements to  
eye aperture and  
voltage level



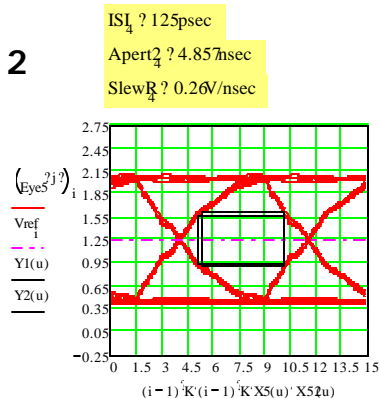
Compensated



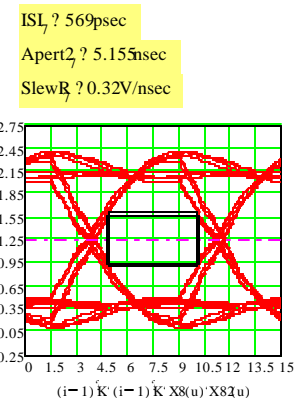
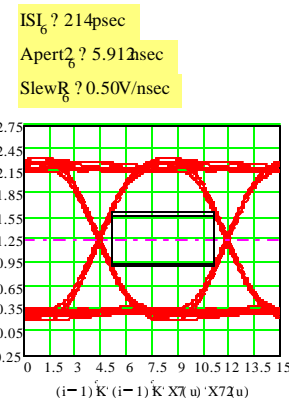
Split Bus



Slot 2



Improvements to  
eye aperture and  
voltage level





# Worst-Case Scenarios

Bus Type	ISI (ps)	Loading	APT2 (ns)	Loading	Min Amp (V)	Loading
Standard	1880	(5,18)	3.664	(5,18)	-0.261	(5,0)
Standard with 10 stub on 5 device	1110	(5,18)	3.774	(5,18)	0.44	(5,0)
Compensated with 10 stub on 5 device	789	(5,18)	5.473	(5,18)	-0.078	(5,18)
Split bus	637	(18,18)	5.125	(18,18)	-0.134	(5,0)
Split bus with 10 stub on 5 device	637	(18,18)	5.125	(18,18)	0.138	(5,0)

ISI = Timing skew due to Inter-symbol interference

APT2 = Data eye time at  $\pm 350\text{ps}$  from  $V_{\text{REF}}$

Min Amp = Undershoot voltage amplitude (overshoot)


Loading = Module load condition of worst case measurement



# Design Impact




## Compensated Bus

- ? Replace RS with capacitor
- ? Systems that only use RS must add RT
- ? Chip-capacitors best solution and lower cost than C-pack for C/A
- ? 18 caps and 5 R-packs
  -  Adds about \$0.14 US
- ? Adds 500ps - 1ns of propagation delay to C/A signals



## Split Bus

- ? 18 additional lines to terminate
- ? 9 additional R-packs for RS and RT
  -  Adds about \$0.09 US
- ? No change in propagation delay





# Conclusions

- ❖ **Compensated scheme and Split Bus provide dramatic improvements in timing and signal integrity**
  - ? Both are very cost effective solutions for high performance memory
  - ? No added cost for motherboard, just a little extra layout time

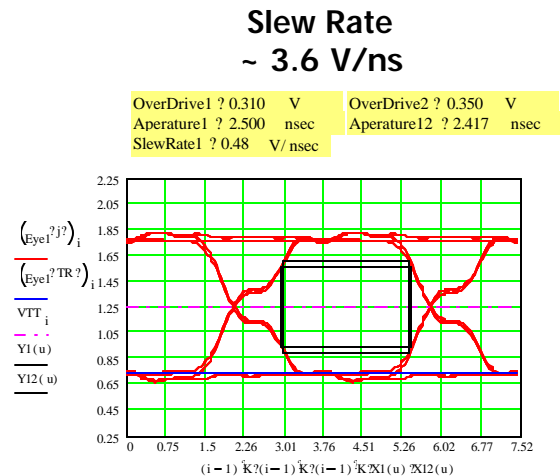


# Improving Read Data Eye Margin

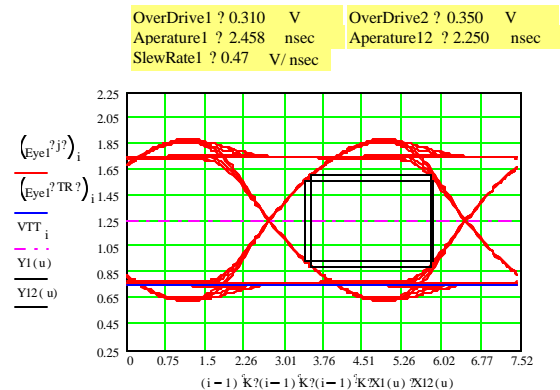


# Active Termination in Northbridge

Standard Termination



Compensated With Active Termination



Even with new termination, reads can benefit from improved system margins



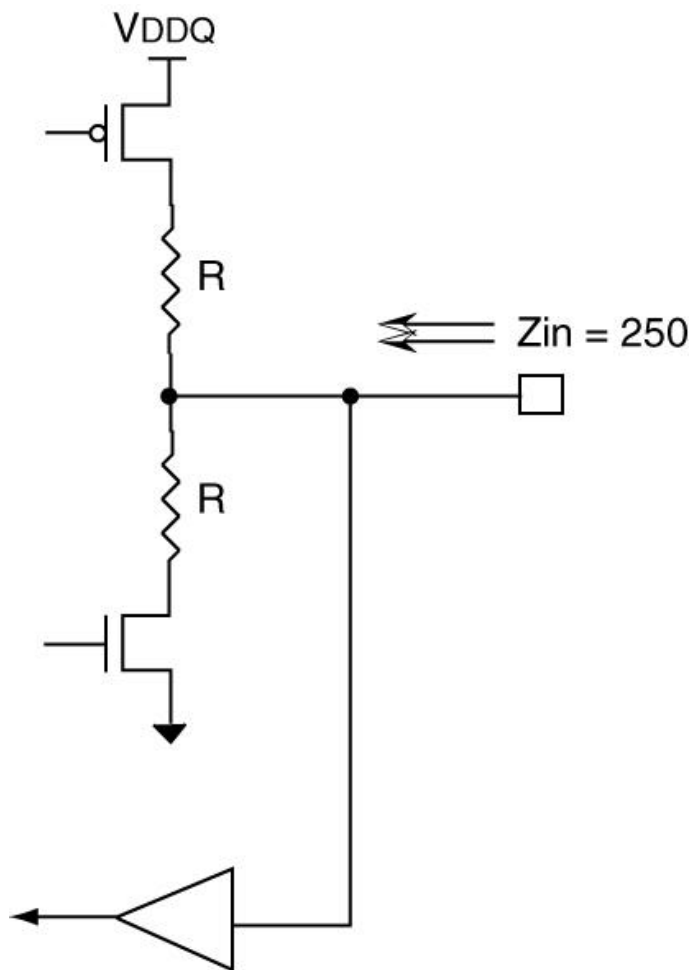
Provides robust system for PC2700 modules



Adds little cost, if any, to ASIC



# Active Termination Implementation



Input impedance of about 250 ohms works well

? Signal integrity is not highly sensitive to the absolute value

FETs on the far side of the resistors (from the pad) will reduce effective input capacitance

Especially beneficial in 3 and 4-DIMM systems



# DDR Migration to PC2700



# PC2700

## Unbuffered system requirements

- ? 1T command rate must be supported

- ? Two assumptions

  -  2 C/A copy, 1T, 2 Unbuffered DIMMs, options for termination

  -  1 C/A copy, 1T, 2 Unbuffered DIMMs, new termination

- ? Support for TSOP and FBGA packages

- ? Component must be speed sort of current SDRAM designs

  -  Keep costs down



# PC2700 Modules



## Unbuffered

- ? FBGA-based can be as low at 1" height



## Registered

- ? 1.125" max height
- ? FBGA-based only, no stacking



## SODIMM

- ? Could be TSOP or FBGA



## MicroDIMM

- ? Most likely to be FBGA-based





# PC2700 Schedule

 **Prototype/samples of standard**

? 3Q01 - 256Mb

 **Validation and qual**

? 3Q01 - 256Mb

 **Production**

? 1Q01 seen as the required need

 **Price of PC2700 = PC2100?**

? 2H02 estimated





# Summary

## **DDR standard updates**

- ? New SPDs

## **Necessity of mixed DDR/SDR systems**

- ? Good way to transition, but be careful

## **New termination schemes to increase performance**

- ? Big gains in timing/noise margin, little added cost

## **Proposal to improved read data capture**

- ? Easy addition to chipset driver to improve reads

## **PC2700 development will be complete this year**